

FOR USE BY ELECTRICIANS OVERSEAS :

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 ($T_b=25^{\circ}\text{C}$)					電 気 的 特 性 ($T_b=25^{\circ}\text{C}$)										外 形	備 考
				V_{ce0} (V)	V_{be0} (V)	I_c (mA)	P_c (mW)	T_j ($^{\circ}\text{C}$)	I_{cbo} 最大値 (μA)	直流又はパルス h_{FE}		バイアス		h_{FE}	h_{ie} h_{ie}^* (Ω)	h_{re} h_{re}^* ($\times 10^{-4}$)	h_{oe} h_{oe}^* (μS)	f_{α} f_{β}^* (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE} , I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB} , I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
 - 9 $f_{\alpha b}$ OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T .
 - 10 C_{ob} AND $r_{bb'}$ OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN $r_{bb'}$ COLUMN WHICH INDICATES VALUE OF $h_{ie}(\text{real})$
 - 11 OUTLINE
 - 12 REMARKS
- : とコンプリ : COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 ($T_a = 25^\circ\text{C}$)					電 気 的 特 性 ($T_a = 25^\circ\text{C}$)											外 形	備 考								
				V_{CB0} (V)	V_{EB0} (V)	I_C (mA)	P_C (mW)	T_j ($^\circ\text{C}$)	IC0 最大値		直流又はハルス hFE			バイアス		h_{fe} h_{fb}^*	h_{ie} h_{ib}^* (Ω)	h_{re} h_{rb}^* ($\times 10^{-4}$)	h_{or} h_{ob}^* (μU)			$f_{\alpha\beta}$ f_T^* (Mc)	C_{ob} (pF)	r_{bb} $r_{bb(\text{real})}^*$ (Ω)					
									I_{CB} (μA)	V_{CB} (V)	V_{CE} (V)	I_C (mA)	V_{CB} (V)	I_E (mA)	h_{FE}										V_{BE} (V)	I_E (mA)			
2SC2652																													
" 2653	松下	SW	Si.TP	350	7.5	200	15W ($T_c=25^\circ\text{C}$)	150	2	200	40~250	10	10	30	-10											161	水平偏向用		
" 2654																													
" 2655	東芝	PA	Si.E	50	5	2A	900	150	1	50	70~240	2	500	2	-500	$t_{on}=0.1\mu\text{S}$, $t_{off}=0.1\mu\text{S}$											241	2SA1020 とコンプリ	
" 2656	富士電機	SW	Si.TP	450	7	7A	80W ($T_c=25^\circ\text{C}$)	150	1mA	450	>10	4	3A			$t_{on}<1.5\mu\text{S}$, $t_{off}<1.5\mu\text{S}$												220	
" 2657	松下	"	Si.TMe	800	8	1.5A	70W ($T_c=25^\circ\text{C}$)	150	100	800	>8	5	1A			$t_{on}<1\mu\text{S}$, $t_{off}<1.2\mu\text{S}$												102	
" 2658	"	"	"	800	8	5A	90W ($T_c=25^\circ\text{C}$)	150	100	800	>8	5	3A			$t_{on}<1\mu\text{S}$, $t_{off}<3\mu\text{S}$												102	
" 2659	"	"	"	800	8	7A	120W ($T_c=25^\circ\text{C}$)	150	100	800	>8	5	5A			$t_{on}<1\mu\text{S}$, $t_{off}<3\mu\text{S}$												102	
" 2660	"	PA	Si.TP	200	6	2A	30W ($T_c=25^\circ\text{C}$)	150	50	200	60~200	10	400			$t_{on}<2.5\mu\text{S}$											268	2SA1133 とコンプリ	
" 2661																													
" 2662	東芝	RF.SW	Si.E	100	12	3A	8W ($T_c=25^\circ\text{C}$)	150	0.1	100	90	2	1A	10	-50													84B	
" 2663																													
" 2664																													
" 2665	サンケン	PA	Si.TMe	100	6	4A	55W ($T_c=25^\circ\text{C}$)	150	1mA	100	90	4	1A	12	-200													324	
" 2666	東芝	"	Si.E	35	3.5	3.5A	30W ($T_c=25^\circ\text{C}$)	175	1mA	15	50	5	1A			$P_D=7\text{W}$ ($f=270\text{MHz}$, $V_{CC}=12.6\text{V}$, $P_1=1\text{W}$)												260	
" 2667	"	"	"	35	3.5	6A	45W ($T_c=25^\circ\text{C}$)	175	1mA	15	50	5	3A			$P_D=20\text{W}$ ($f=270\text{MHz}$, $V_{CC}=12.6\text{V}$, $P_1=6\text{W}$)												260	
" 2668	"	RF.Mix. Conv.	Si.EP	40	4	20	100	125	0.5	40	40~200	6	1	6	-1	$G_{m1}=18\text{dB}$, $NF=2.5\text{dB}$ (6V , 1mA , 100MHz)	550*	C_{re} 0.7	$C_{r_{\alpha\beta}}$ <30pS								287		
" 2669	"	"	"	35	4	50	200	125	0.1	35	40~240	12	2	10	-1	$G_{m2}=30\text{dB}$ (6V , 1mA , 10.7MHz)	>100*	2	$C_{r_{\alpha\beta}}$ <50pS								287		
" 2670	"	"	Si.E	35	4	100	200	125	0.1	35	40~240	12	2	10	-2	$NF=2\text{dB}$ (10V , 1mA , 1MHz)	>80*	C_{re} 2.2	$C_{r_{\alpha\beta}}$ <50pS								287		
" 2671	松下	RF	Si.EP	25	3	70	250	150	0.1	10	40~200	10	20															138C	
" 2672																													
" 2673																													
" 2674																													
" 2675																													
" 2676	日電	RF.LN	Si.E	80		10	500	125	0.1	70	400	6	1	6	-1	$NF=1.5\text{dB}$ (5V , 1mA , 1kHz)	200*	1.2	$C_{r_{\alpha\beta}}$ 85pS								278		
" 2677	日立	RF.Conv. Mix.Osc	Si.P	30	5	100	625	125	1	18	160	12	2	12	-1													138D	
" 2678	"	"	"	20	3	30	500	125	1	10	100	6	1	6	-6													138D	
" 2679	"	Osc	Si.EP	30	2	50	300	125	0.5	10	80	10	10	10	-10	$P_{acc}=8\text{mW}$ ($V_{CB}=10\text{V}$, $I_C=10\text{mA}$, $f=930\text{MHz}$)	1000*	1.2	$C_{r_{\alpha\beta}}$ 10pS								138D		
" 2680	松下	RF	"	40	4	30	200	125	10	40	>38	10	7	10	-5	$G_{m2}=25\text{dB}$ (6V , 7mA , 58MHz)	550*	C_{re} 0.37									176		
" 2681	日電	PA	Si.T	115	5	10A	100W ($T_c=25^\circ\text{C}$)	150	50	80	140	2	1A	2	-1A													162	2SA1141 とコンプリ